

**ATTACHMENT FOR CLAIM AMENDMENTS**

The following is a marked up version of each amended claim in which underlines indicates insertions and brackets indicate deletions.

2. (Amended) The method for the fabrication of a field-effect transistor according to claim 1, wherein heat treatment of said gate insulating film[ ] is[ ] conducted at a temperature of no less than 100°C.

3. (Amended) The method for the fabrication of a field-effect transistor according to claim 1, wherein the formation of said gate insulating film[ ] is[ ] conducted while heating of said substrate is being prohibited.

4. (Amended) The method for the fabrication of a field-effect transistor according to claim 1, wherein the formation of said gate insulating film[ ] is[ ] conducted while said substrate is being cooled to a temperature of no higher than room temperature.

5. (Amended) The method for the fabrication of a field-effect transistor according to claim 1, wherein said gate insulating film[ ] is [ ] formed by a plasma CVD method.

6. (Amended) The method for the fabrication of a field-effect transistor according to claim 1, wherein said gate insulating film[ ] is[ ] formed by a microwave plasma CVD method.

9. (Amended) The method for the fabrication of a field-effect transistor according to claim 8, wherein heat treating of said gate insulating film[ ] is[ ] conducted at a temperature of no less than 100[.]°C.

10. (Amended) The method for the fabrication of a field-effect transistor according to claim 7, wherein the formation of said first-stage gate insulating film[ ] is[ ] conducted while heating of said substrate is being prohibited.

11. (Amended) The method for the fabrication of a field-effect transistor according to claim 7, wherein the formation of said first-stage gate insulating film[ ] is[ ] conducted while said substrate is being cooled to a temperature of no higher than room temperature.

12. (Amended) The method for the fabrication of a field-effect transistor according to claim 7, wherein the formation of said first-stage gate insulating film[ ] is[ ] conducted by a plasma CVD method.

13. (Amended) The method for the fabrication of a field-effect transistor according to claim 7, wherein the formation of said first-stage gate insulating film[ ] is[ ] conducted by a microwave plasma CVD method.

14. (Amended) The method for the fabrication of a field-effect transistor according to claim 7, wherein the formation of said second-stage insulating film[ ] is[ ] conducted by a plasma CVD method using TEOS gas.